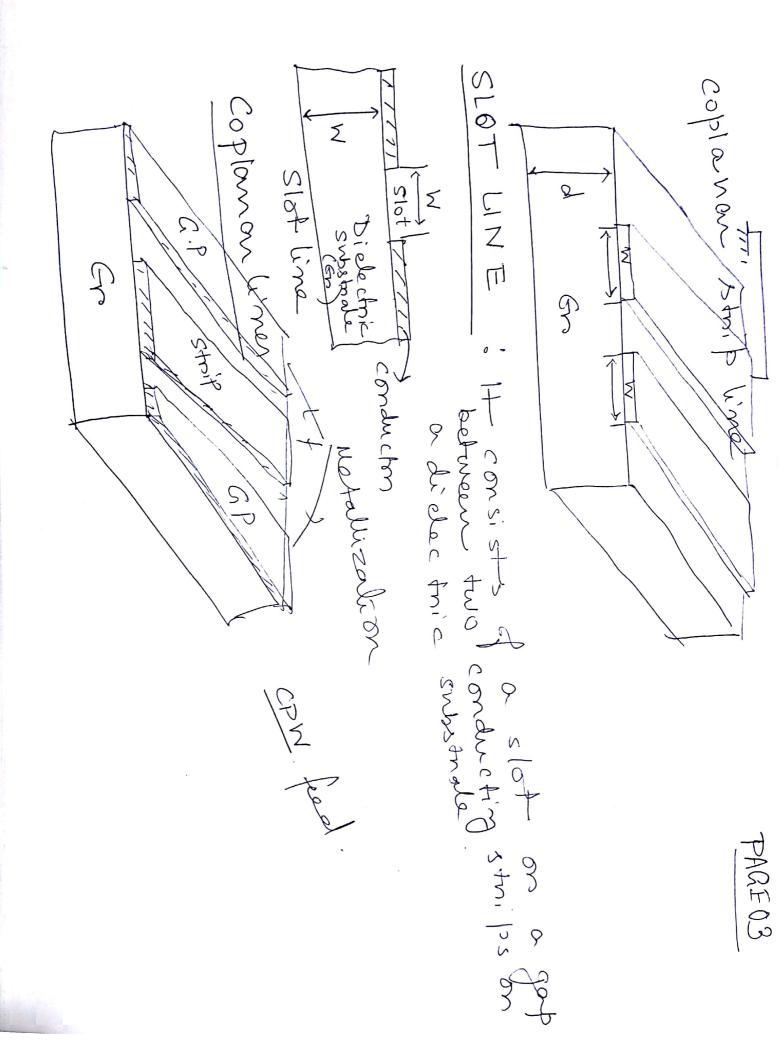
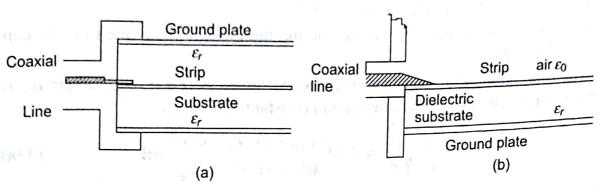


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electromagnetic energy. The radiation loss is proportional to the square of the frequency. The use of thin and high dielectric materials reduces the radiation loss of the open structure where the fields are mostly confined inside the dielectric.



Strip line launcher connector (a) Strip line connector Fig. 3.19 (b) Microstrip line connector

Effective Dielectric Constant

Since the propagation field lines in a microstrip lie partially in air and partially inside the homogenous dielectric substrate, the propagation delay time for a quasi-TEM mode is related to an effective dielectric constant $\varepsilon_{\rm eff}$, given by

$$\varepsilon_{\text{eff}} = \frac{\varepsilon_r + 1}{2} + \frac{\varepsilon_r - 1}{2} \left[\left(1 + \frac{12h}{W} \right)^{-1/2} + 0.04 \left(1 - \frac{W}{h} \right)^2 \right]; W/h \le 1$$
 (3.84)

$$\varepsilon_{\text{eff}} = \frac{\varepsilon_r + 1}{2} + \frac{\varepsilon_r - 1}{2} \left(1 + \frac{12h}{W} \right)^{-1/2}; W/h \gg 1$$
(3.85)

where ε_r is the relative dielectric constant of the substrate material.

Characteristic Impedance and Guide Wavelength

The characteristic impedance of microstrip lines can be expressed by

characteristic impedance of incrossisperson
$$Z_0 = \frac{60}{\sqrt{\varepsilon_{\text{eff}}}} \ln \left[\frac{8h}{W} + \frac{W}{4h} \right] \text{ ohm, } W/h \le 1$$
(3.86)

$$Z_0 = \frac{376.7}{\sqrt{\varepsilon_{\text{eff}} \left[\frac{W}{h} + 1.4 + 0.667 \ln \left(\frac{W}{h} + 1.444 \right) \right]}} \text{ ohm; for } W/h > 1 \quad (3.87)$$

$$Z_0 = \frac{376.7}{\sqrt{\varepsilon_{\text{eff}}}} \frac{h}{W} \text{ ohm; for } W/h \gg 1$$
 (3.88)

The guide wavelength for the propagation of quasi-TEM mode is given by

$$\lambda_{g} = \lambda_{0} / \sqrt{\varepsilon_{\text{eff}}} \tag{3.89}$$

The characteristic impedance for a microstrip line vs W/h with ε_r as a parameter is plotted in Fig. 3.20. It is seen that the value of Z_0 decreases with increase of W/h and also with increase of ε_r .

When a pure TEM mode is assumed to exist, the method of conformal transformation may be used for the calculation of capacitance in the case of microstrip also. Because of the mixed dielectric configuration the analysis is carried out in two stages. First the capacitance is calculated for a uniform dielectric microstrip line. This result is then extended to cover the real microstrip case simply by replacing the 'uniform' dielectric constant ε_r by the 'effective' dielectric constant ε_{eff} . The concept of effective dielectric constant is explained in Fig. 10.6 (b). Wheeler (1965) has given a conformal transformation useful for microstrip analysis and derived micro-strip design formulas based on that. These consist of two different relations for wide (W/h > 2) and narrow (W/h < 2) microstrip lines because of the different approximations used. Recently (Wheeler, 1977) an empirical relation that covers both the ranges has been reported and may be written as

$$\frac{W}{h} = 8 \frac{\{ [\exp Z_0 \sqrt{\varepsilon_r + 1/42.4 - 1}] (7 + 4/\varepsilon_r)/11 + (1 + 1/\varepsilon_r)/0.81 \}^{1/2}}{\exp \{ (Z_0 \sqrt{\varepsilon_r + 1/42.4}) - 1 \}} \dots (10.14)$$

Relation (10.14) is suitable for design (or synthesis). For analysis it may be reversed and put in the following form

$$Z_{0} = \frac{42.4}{\sqrt{\varepsilon_{r} + 1}} \ln \left\{ 1 + \left(\frac{4h}{W} \right) \left[\left(\frac{14 + 8/\varepsilon_{r}}{11} \right) \left(\frac{4h}{W} \right) + \sqrt{\left(\frac{14 + 8/\varepsilon_{r}}{11} \right)^{2} \left(\frac{4h}{W} \right)^{2} + \frac{1 + 1/\varepsilon_{r}}{2} \pi^{2}} \right] \qquad \dots (10.15)$$

Effective dielectric constant may be found by evaluating an additional value of Z_0 for $\varepsilon_r = 1$. We have

$$\varepsilon_{\text{eff}} = \left(\frac{Z_0(\varepsilon_r = 1)}{Z_0}\right)^2 \qquad \dots (10.16a)$$

Alternatively, an empirical expression (Schneider, 1969) gives ε_{eff} directly in terms of ε_{r} W and h. This may be written as

$$\varepsilon_{\text{eff}} = \frac{\varepsilon_r + 1}{2} + \frac{\varepsilon_r - 1}{2} \left(1 + \frac{10h}{W} \right)^{-1/2} \qquad \dots (10.16b)$$

Variation of microstrip characteristic impedance with W/h is shown in Fig. 10.7. It may be noted that for microstrip lines, the phase velocity v_p is given by

$$v_p = c/\sqrt{\varepsilon_{\rm eff}} \qquad \dots (10.17)$$

Since ε_{eff} is a function of W and h, the phase velocity and hence the guide wavelength depends upon the line impedance also. This factor has to be taken into account while designing microstrip circuits.